

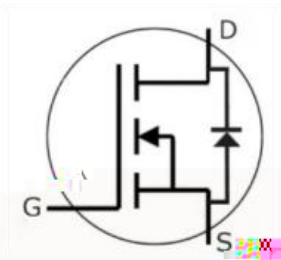
S3M009075V1K-A



TriQSiC™750V Silicon Carbide Power MOSFET G3

Features

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-
-
-
-



Benefits

-
-
-
-
-

Part number	Die size	W x L	mm

Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V _{DS}	I _{DS}	R _{DS(on)} , typ	T _{J,max}

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Features1

Benefits

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1 Maximum ratings

Table 2 **Maximum rating**

Symbol	Parameter	Value	Unit	Test Conditions	Note

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2 Electrical characteristics

2.1 Static characteristics

Table 4 Static characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

2.2 Dynamic characteristics

Table 5 Dynamic characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
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2.3 Switching characteristics

Table 6 Dynamic characteristics(

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

When the gate voltage is applied, the drain current increases from zero to a steady-state value. The time taken for the drain current to reach the steady-state value is called the turn-on time.

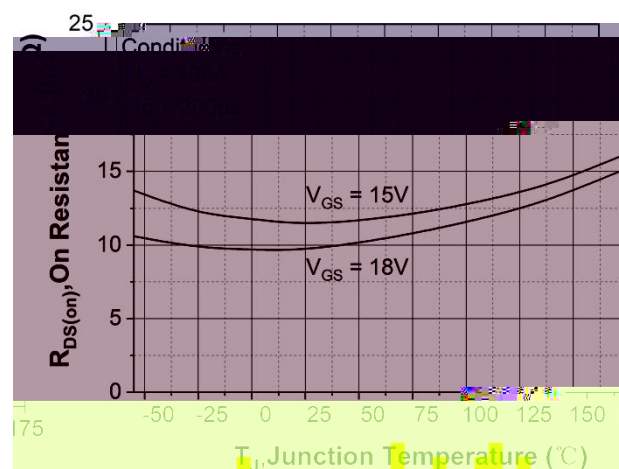
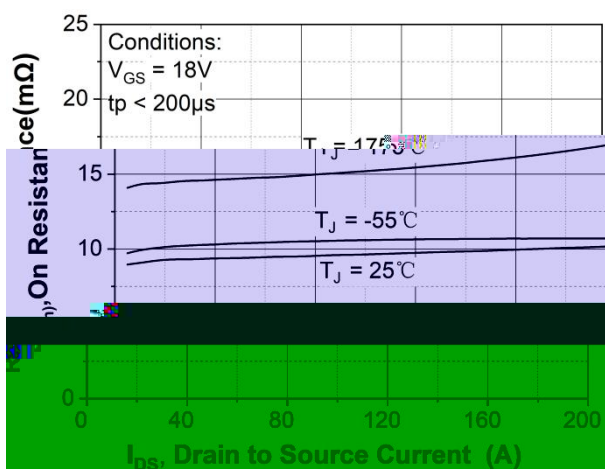
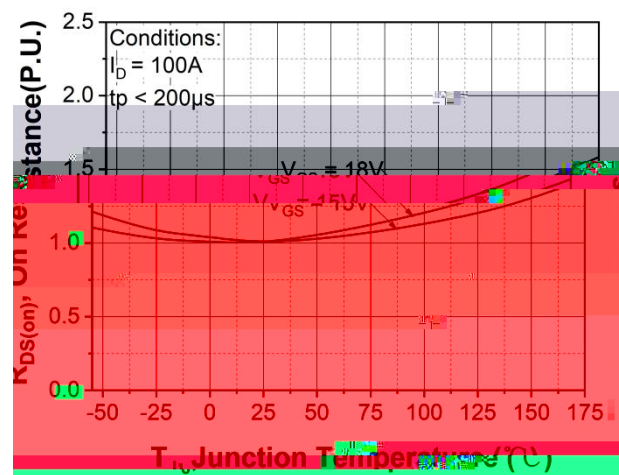
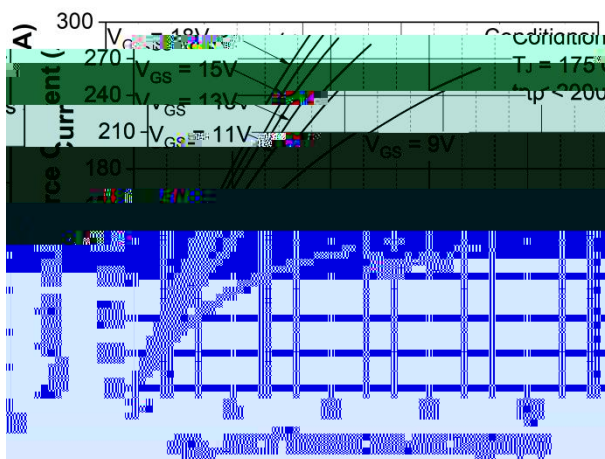
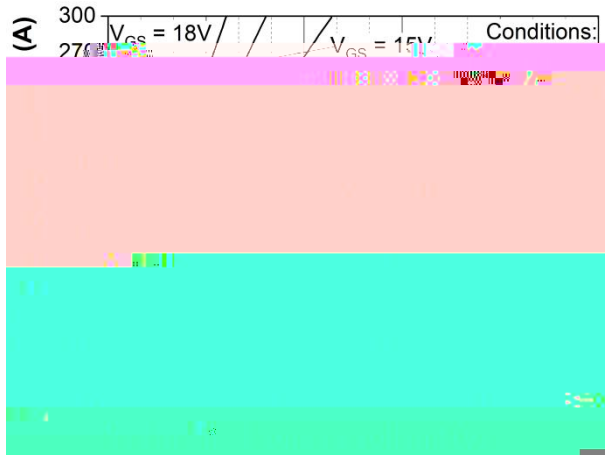


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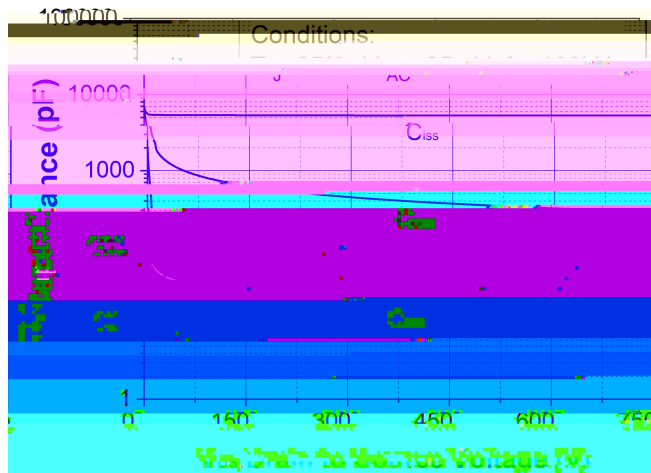
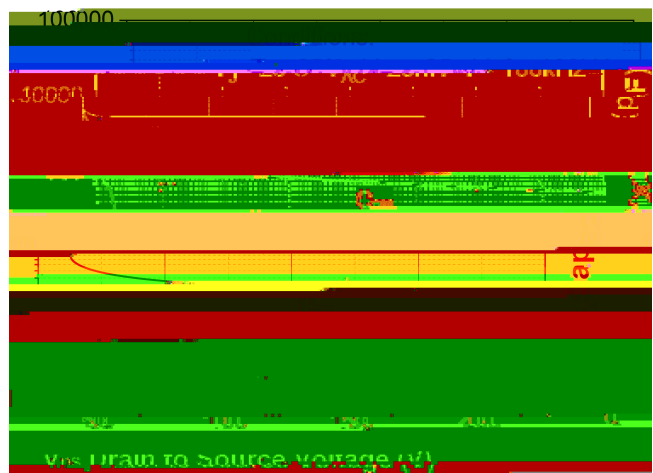
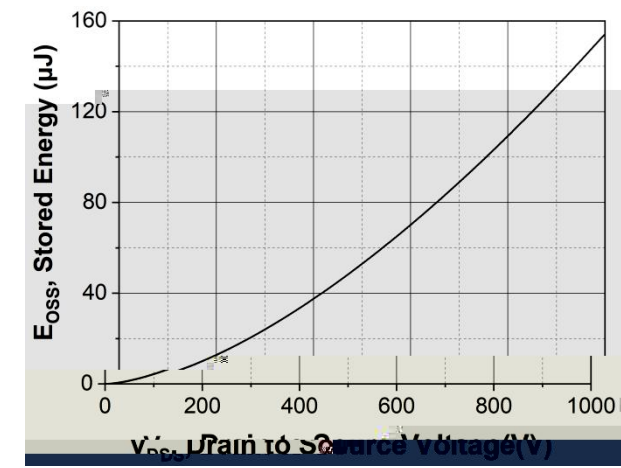
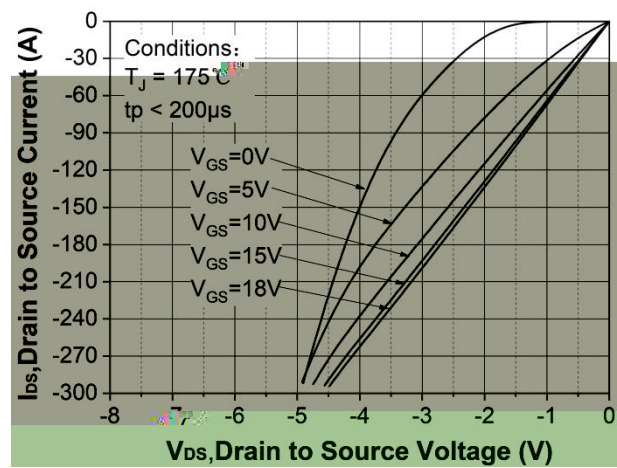
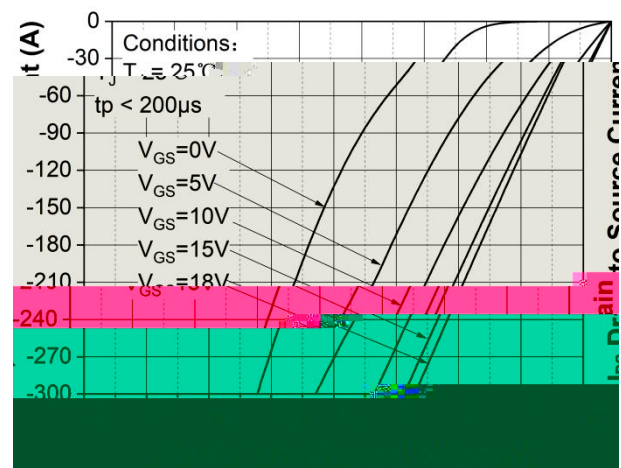
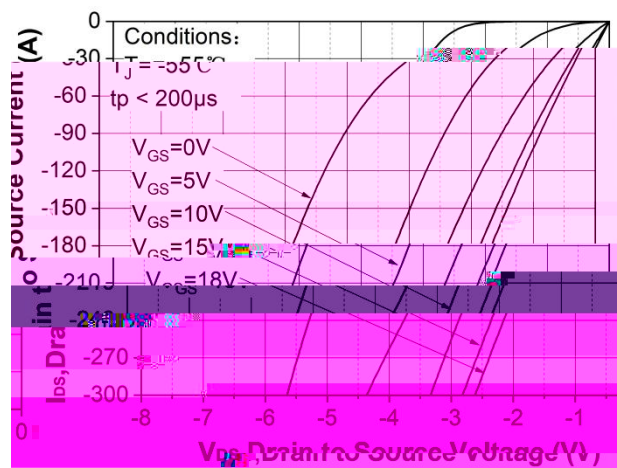
3 Electrical characteristic diagrams



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4 Mechanical parameters

[illegible][illegible]

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Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2026-06-26	Final	

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